

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently amended) A dry etching method for dry-etching a Cu-containing aluminum film on a substrate held in a chamber by introducing etching gas containing at least chlorine in said chamber to generate plasma,

wherein a gas stay time τ ($= P \cdot V/Q$) is ~~from~~ controlled between 0.15 seconds to 0.30 seconds inclusive, such that no residue of copper composing said Cu-containing aluminum film is generated, said gas is a mixture gas composed of said etching gas and an aluminum chloride, which is a reaction product of said Cu-containing aluminum film and said etching gas, P being a pressure in said chamber (unit: Pa), V being a volume of said chamber (unit: L) and Q being a total etching gas flow (unit: Pa • L/sec).

2. (Original) The dry etching method according to claim 1, wherein said substrate is a wafer having a diameter of 20cm, and the volume of said chamber is from 30L to 35L inclusive.

3. (Original) The dry etching method according to claim 2, wherein the total etching gas flow is from 60mL/min (at the standard state) to 240mL/min (at the standard state) inclusive.

4. (Original) The dry etching method according to claim 1, wherein said substrate is a wafer having a diameter of 30cm, and the volume of said chamber is from 60L to 70L inclusive.

5. (Original) The dry etching method according to claim 4, wherein the total etching gas flow is from 120mL/min (at the standard state) to 480mL/min (at the

standard state) inclusive.

6. (Currently amended) A dry etching method for dry-etching a Cu-containing aluminum film on a substrate held in a chamber by introducing etching gas containing at least chlorine in said chamber to generate plasma,

wherein a gas stay time τ ($= P \cdot V/Q$, where $0.93 \leq P \leq 1.86$)) is ~~from~~ controlled between 0.15 seconds to 0.30 seconds inclusive, such that no residue of copper composing said Cu-containing aluminum film is generated, said gas is a mixture gas composed of said etching gas and an aluminum chloride, which is a reaction product of said Cu-containing aluminum film and said etching gas, P being a pressure in said chamber (unit: Pa), V being a volume of said chamber (unit: L) and Q being a total etching gas flow (unit: Pa • L/sec).

7. (Original) The dry etching method according to claim 6, wherein said substrate is a wafer having a diameter of 20cm, and the volume of said chamber is from 30L to 35L inclusive.

8. (Original) The dry etching method according to claim 7, wherein the total etching gas flow is from 60mL/min (at the standard state) to 240mL/min (at the standard state) inclusive.

9. (Original) The dry etching method according to claim 6, wherein said substrate is a wafer having a diameter of 30cm, and the volume of said chamber is from 60L to 70L inclusive.

10. (Original) The dry etching method according to claim 9, wherein the total etching gas flow is from 120mL/min (at the standard state) to 480mL/min (at the standard state) inclusive.